NSN 5961-00-419-7550

Diode Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-00-419-7550
Inclosure Material:
Metal
Overall Length:
1.253 inches
Mounting Facility Quantity:
1
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
Do-4
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
Between 0.423 inches and 0.438 inches
Thread Size:
0.190 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
36.0 regulator voltage
Voltage Tolerance In Percent:
-5.0/+5.0
Current Rating Per Characteristic:
70.00 milliamperes all primaries horsepower metric and 260.00 milliamperes repetitive peak forward current
Power Rating Per Characteristic:
10.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius junction
Test Data Document:
81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designator:
Unf
Terminal Type And Quantity:
1 tab, solder lug and 1 threaded stud
Specification Data:
81349-mil-prf-19500/124 government specification
Shelf Life:
N/a

Unit Of Measure:

NSN 5961-00-419-7550

Diode Semiconductor Device - Page 2 of 2



Demilitarization:

No

Fiig:

A110a0

Mil-std (military Standard):

Mil-prf-19500 spec.